

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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GBL06 thru GBL10

Silicon Bridge Rectifier

 $V_{RRM} = 50 \text{ V} - 1000 \text{ V}$ $I_F = 4 \text{ A}$

Features

 Plastic package has Underwriters Laboratory Flammability Classification 94V-0

 \bullet Types up to 1000 V V_{RRM}

· Ideal for printed circuit board

· High surge current capability

• High temperature soldering guaranteed: 250°C/ 10 seconds, 0.375(9.5mm) lead length

· Glass passivated chip junction

· High case dielectric strength

Mechanical Data

Case: Molded plastic body over passivated junctions

Weight: 0.071 oz, 2 g Mounting position: Any

Terminals: Plated leads, solderable per MIL-STD-750

Method 2026 guaranteed





Maximum ratings, at T_i = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	GBL06	GBL08	GBL10	Unit
Repetitive peak reverse voltage	V_{RRM}		600	800	1000	V
RMS reverse voltage	V_{RMS}		420	560	700	V
DC blocking voltage	V_{DC}		600	800	1000	V
Continuous forward current	I _F	T _C ≤ 25 °C	4	4	4	Α
Surge non-repetitive forward current, Half Sine Wave	I _{F,SM}	$T_C = 25 ^{\circ}\text{C}, t_p = 8.3 \text{ms}$	150	150	150	Α
Operating temperature	Tj		-55 to 150	-55 to 150	-55 to 150	°C
Storage temperature	T _{stg}		-55 to 150	-55 to 150	-55 to 150	°C

Electrical characteristics, at Tj = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	GBL06	GBL08	GBL10	Unit
Diode forward voltage	V _F	I _F = 4 A, T _j = 25 °C	1.1	1.1	1.1	V
Reverse current	I _R	V _R = 50 V, T _j = 25 °C	5	5	5	μΑ
		$V_R = 50 \text{ V}, T_j = 125 ^{\circ}\text{C}$	500	500	500	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJA}		22.0	22.0	22.0	°C/W
	R_{thJL}		3.5	3.5	3.5	















